The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS® Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

GreenMOS®

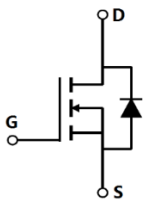
RoHS

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	750	V
$I_{D,\ pulse}$	36	A
$R_{DS(ON)\ ,\ max}$ @ V_{GS}=10V	350	mΩ
Q_g	16.7	nC

Product Name	Package	Marking
OSG70R350AF	TO251	OSG70R350A



Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	700	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	12	A
Continuous drain current[1], T_C=100 °C		7.6	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	36	A
Continuous diode forward current[1], T_C=25 °C	I_S	12	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	36	A
Power dissipation[3], T_C=25 °C	P_D	104	W
Single pulsed avalanche energy[5]	E_{AS}	400	mJ
MOSFET dv/dt ruggedness, V_{DS}=0…480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}=0…480 V, I_{SD}≤I_D	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.2	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	700			V	V_{GS}=0 V, I_D=250 μA
		750	820			V_{GS}=0 V, I_D=250 μA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		0.3	0.35	Ω	V_{GS}=10 V, I_D=6 A
			0.78			V_{GS}=10 V, I_D=6 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=700 V, V_{GS}=0 V

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}				pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}		63.8		pF	
Reverse transfer capacitance	C_{rss}		2.1		pF	
Turn-on delay time	$t_{d(on)}$		31.1		ns	V_{GS}=10 V, V_{DS}=400 V, R_G=25 Ω, I_D=6 A
Rise time	t_r		16.8		ns	
Turn-off delay time	$t_{d(off)}$		55.4		ns	
Fall time	t_f		24.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		16.7		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=6 A
Gate-source charge	Q_{gs}		4.8		nC	
Gate-drain charge	Q_{gd}		5.3		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	I_S=12 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		284.5		ns	, I_S=6 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		2.9		μC	
Peak reverse recovery current	I_{rrm}		19.4		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=10 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

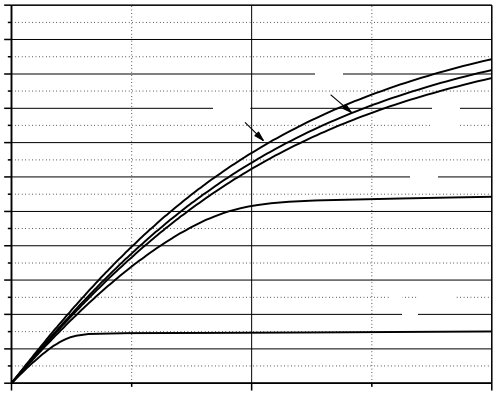


Figure 1. Typ. output characteristics

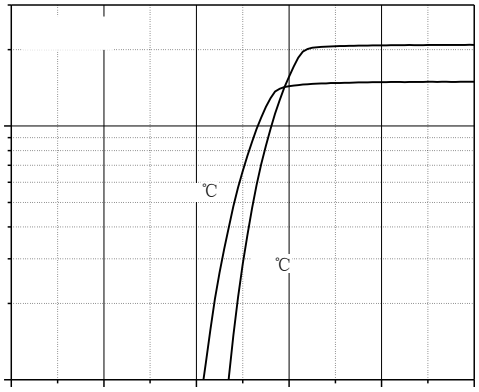


Figure 2. Typ. transfer characteristics

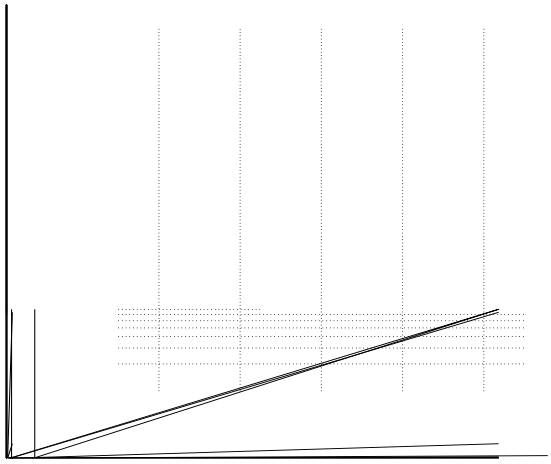


Figure 3. Typ. capacitances

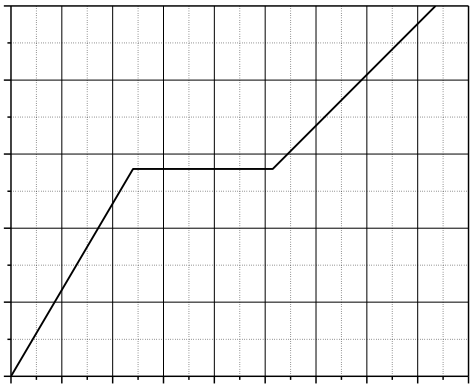


Figure 4. Typ. gate charge

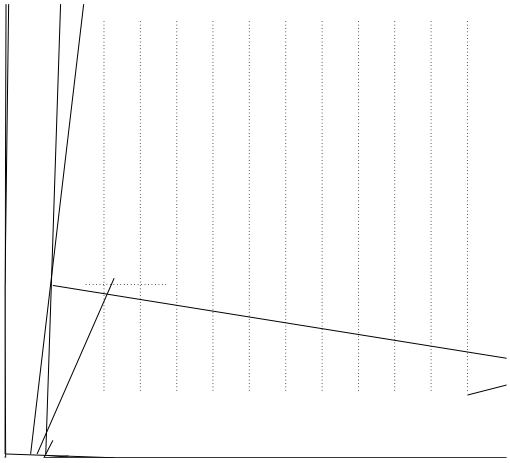


Figure 5. Drain-source breakdown voltage

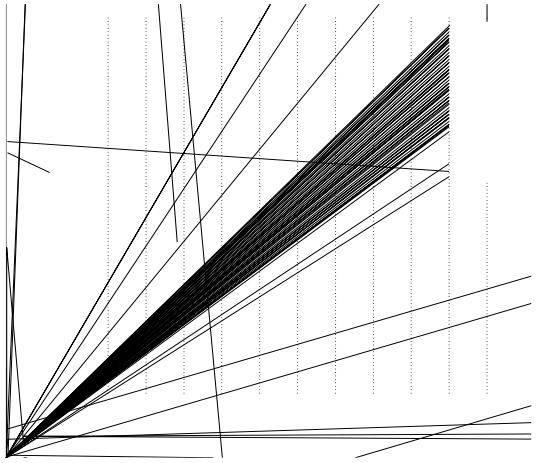


Figure 6. Drain-source on-state resistance

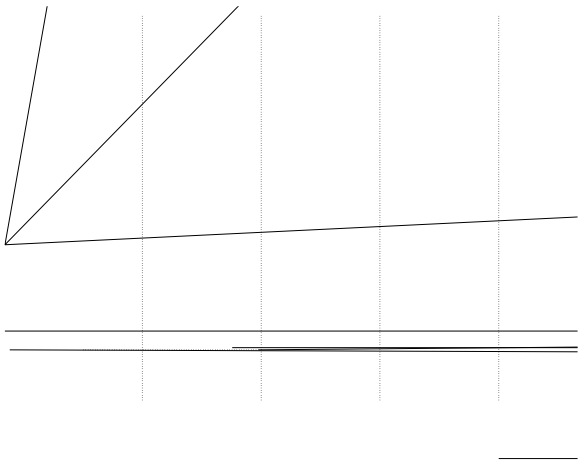


Figure 7. Forward characteristic of body diode

Figure 8. Drain-source on-state resistance

Figure 9. Drain current

Figure 10. Safe operation area T_C=25 °C

Test circuits and waveforms

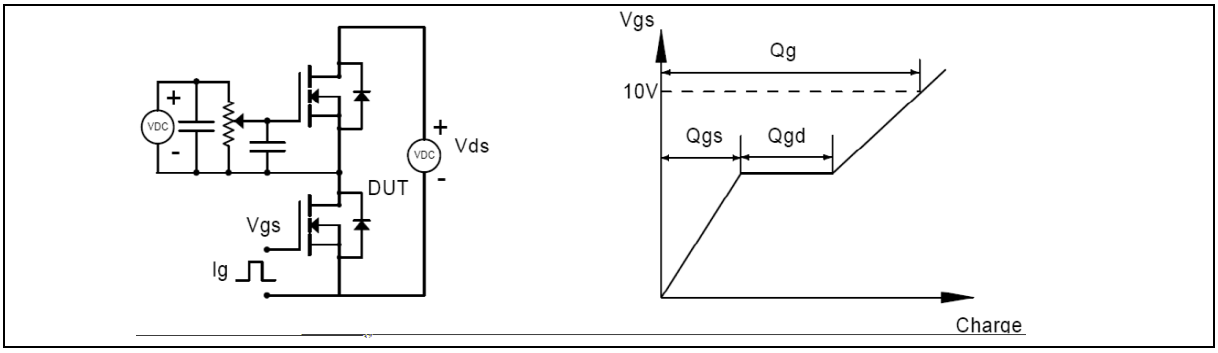


Figure 1. Gate charge test circuit & waveform

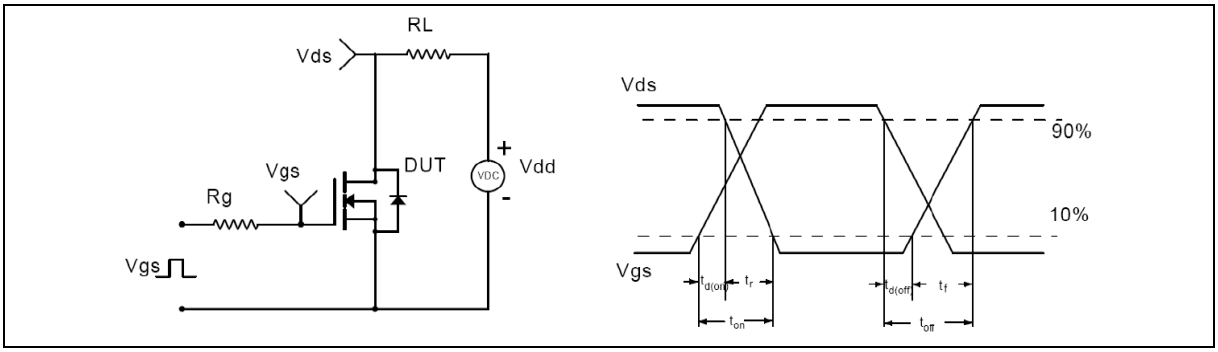


Figure 2. Switching time test circuit & waveforms

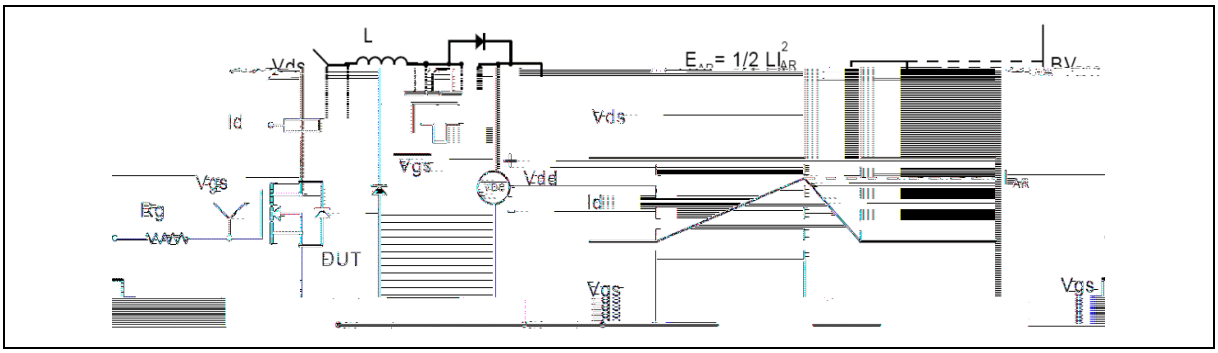


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

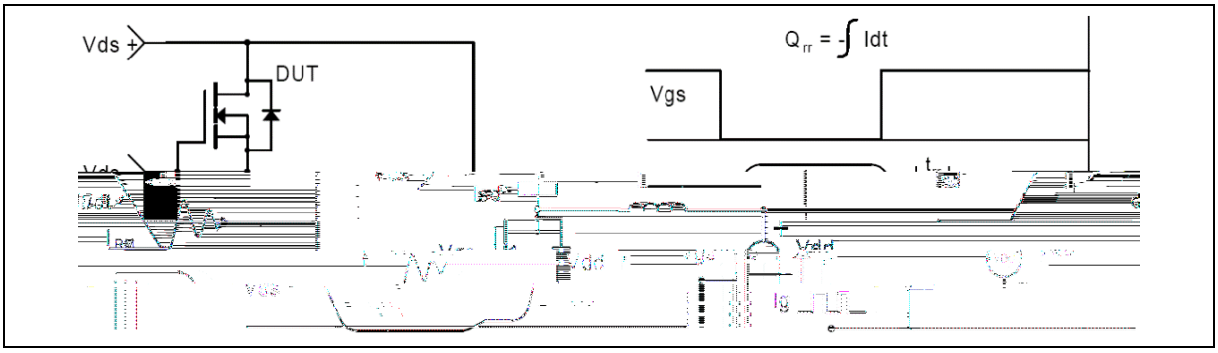


Figure 4. Diode reverse recovery test circuit & waveforms

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO251-C	75	66	4950	6	29700

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG70R350AF	TO251	yes	yes	yes

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